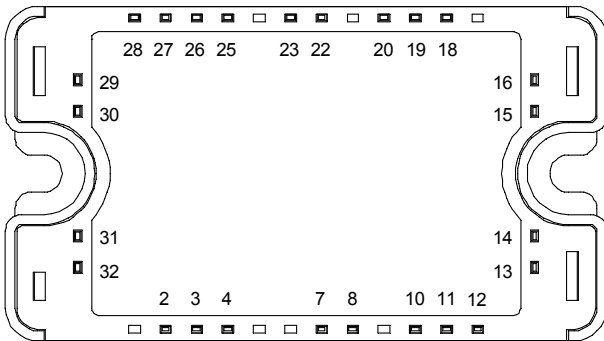
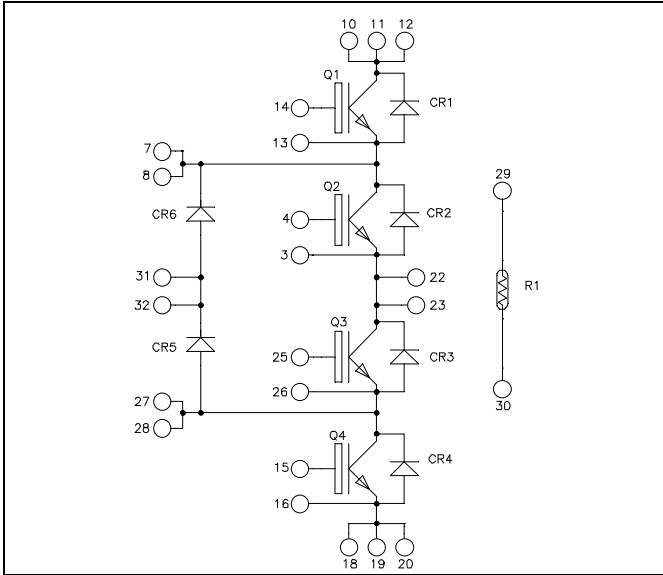


**Three level inverter
Trench + Field Stop IGBT4**

**$V_{CES} = 1200V$
 $I_C = 60A @ T_c = 80^\circ C$**



All multiple inputs and outputs must be shorted together
 Example: 10/11/12 ; 7/8 ...

Application

- Solar converter
- Uninterruptible Power Supplies

Features

- Trench + Field Stop IGBT 4 Technology
 - Low voltage drop
 - Low leakage current
 - Low switching losses
- Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration
- Internal thermistor for temperature monitoring

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS Compliant

Q1 to Q4 Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	1200	V
I_C	Continuous Collector Current	$T_c = 25^\circ C$	80
		$T_c = 80^\circ C$	60
I_{CM}	Pulsed Collector Current	$T_c = 25^\circ C$	100
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	280
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^\circ C$	100A @ 1100V

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.
 See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Q1 to Q4 Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$			1	mA
$V_{CE(sat)}$	Collector Emitter saturation Voltage	$V_{GE} = 15V$ $I_C = 50A$	$T_j = 25^\circ\text{C}$	1.8	2.2	V
			$T_j = 150^\circ\text{C}$	2.2		
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1.6mA$	5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$			400	nA

Q1 to Q4 Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0V$		2770		pF
C_{oes}	Output Capacitance	$V_{CE} = 25V$		205		
C_{res}	Reverse Transfer Capacitance	$f = 1MHz$		160		
Q_G	Gate charge	$V_{GE} = \pm 15V ; V_{CE} = 600V$ $I_C = 50A$		0.38		μC
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = \pm 15V$ $V_{CE} = 600V$ $I_C = 50A$ $R_G = 8.2\Omega$		50		ns
T_r	Rise Time			27		
$T_{d(off)}$	Turn-off Delay Time			270		
T_f	Fall Time			70		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{CE} = 600V$ $I_C = 50A$ $R_G = 8.2\Omega$		50		ns
T_r	Rise Time			30		
$T_{d(off)}$	Turn-off Delay Time			290		
T_f	Fall Time			80		
E_{on}	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{CE} = 600V$ $I_C = 50A$	$T_j = 25^\circ\text{C}$	3.8		mJ
			$T_j = 150^\circ\text{C}$	5.5		
E_{off}	Turn-off Switching Energy	$R_G = 8.2\Omega$	$T_j = 25^\circ\text{C}$	2.5		mJ
			$T_j = 150^\circ\text{C}$	4.5		
I_{sc}	Short Circuit data	$V_{GE} \leq 15V ; V_{Bus} = 900V$ $t_p \leq 10\mu\text{s} ; T_j = 150^\circ\text{C}$		200		A
R_{thJC}	Junction to Case Thermal Resistance				0.53	$^\circ\text{C/W}$

CR1 to CR6 diode ratings and characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>		<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
I _{RM}	Maximum Reverse Leakage Current	V _R =600V	T _j = 25°C T _j = 150°C			100 500	μA
I _F	DC Forward Current		T _c = 80°C		30		A
V _F	Diode Forward Voltage	I _F = 30A			2.6	3.1	V
		I _F = 60A			3.2		
		I _F = 30A	T _j = 125°C		1.8		
t _{rr}	Reverse Recovery Time	I _F = 30A V _R = 800V	T _j = 25°C		300		ns
			T _j = 125°C		380		
Q _{rr}	Reverse Recovery Charge	di/dt = 200A/μs	T _j = 25°C		360		nC
			T _j = 125°C		1700		
E _{rr}	Reverse Recovery Energy	I _F = 30A V _R = 800V di/dt = 1000A/μs	T _j = 125°C		1.6		mJ
R _{thJC}	Junction to Case Thermal Resistance					1.2	°C/W

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

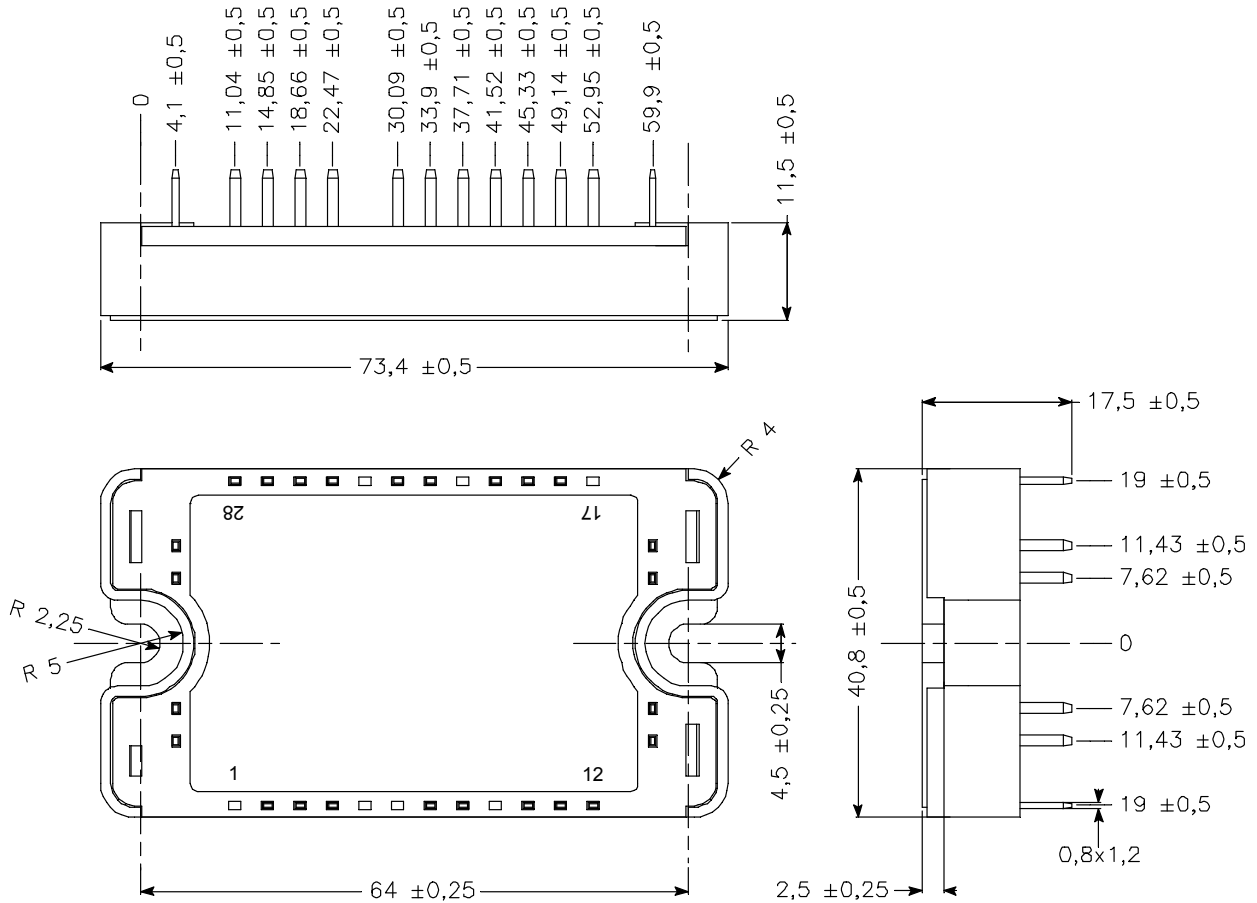
<i>Symbol</i>	<i>Characteristic</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
R ₂₅	Resistance @ 25°C		50		kΩ
ΔR ₂₅ /R ₂₅			5		%
B _{25/85}	T ₂₅ = 298.15 K		3952		K
ΔB/B	T _C = 100°C		4		%

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

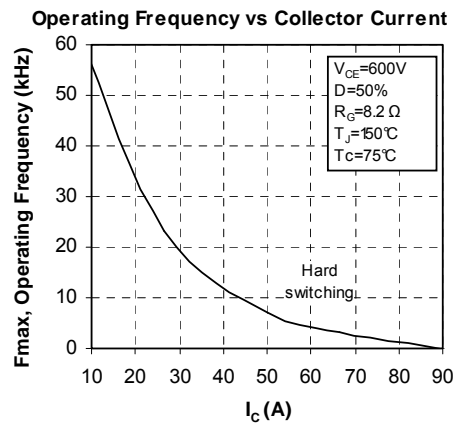
T: Thermistor temperature
R_T: Thermistor value at T

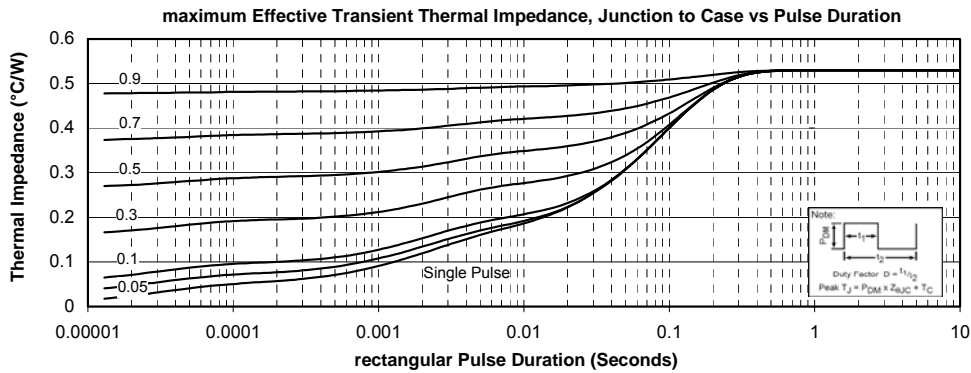
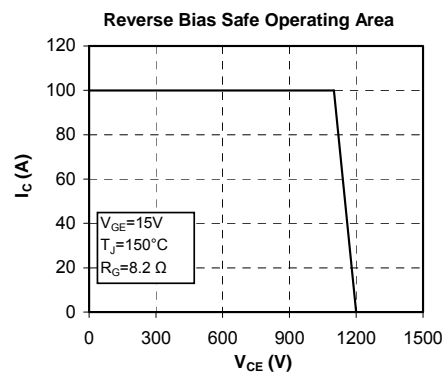
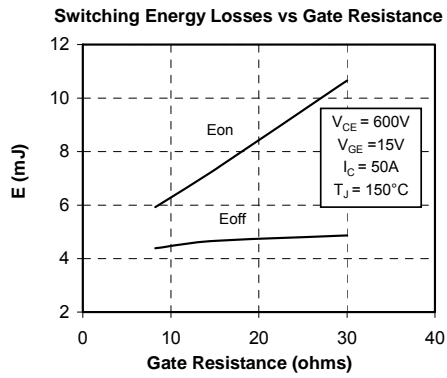
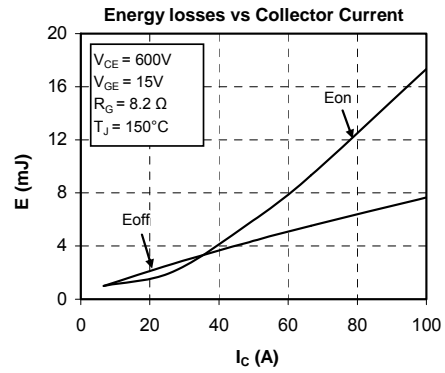
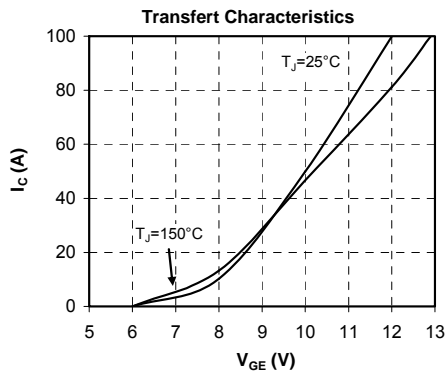
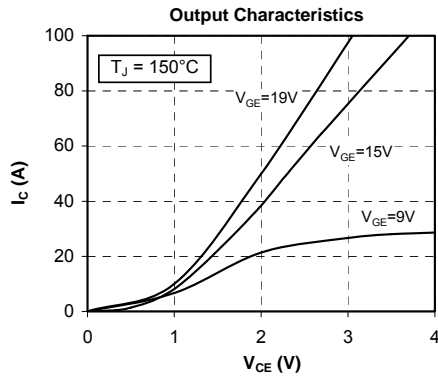
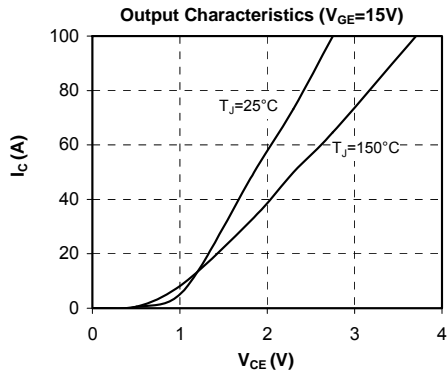
Thermal and package characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, I _{isol} < 1mA, 50/60Hz	2500			V	
T _J	Operating junction temperature range	-40		175	°C	
T _{STG}	Storage Temperature Range	-40		125		
T _C	Operating Case Temperature	-40		100		
Torque	Mounting torque	To heatsink	M4	2.5	4.7	N.m
Wt	Package Weight				110	g

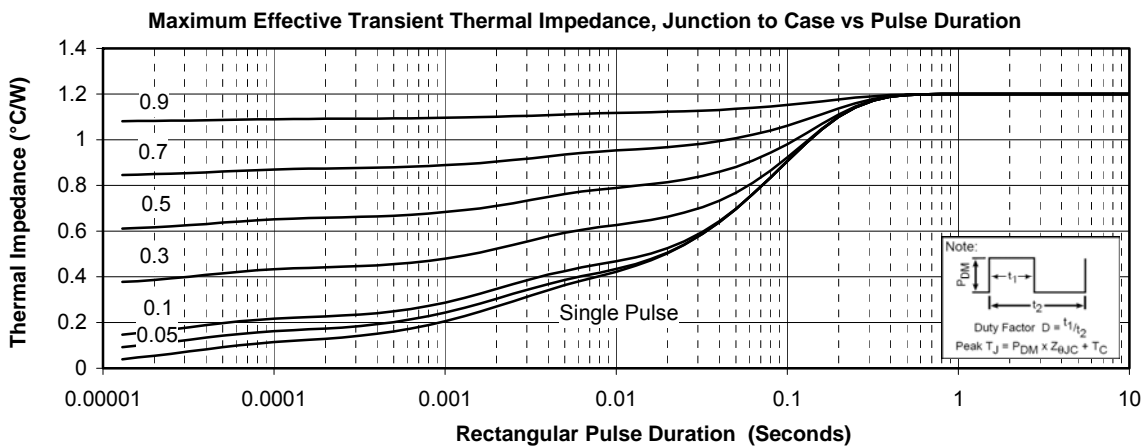
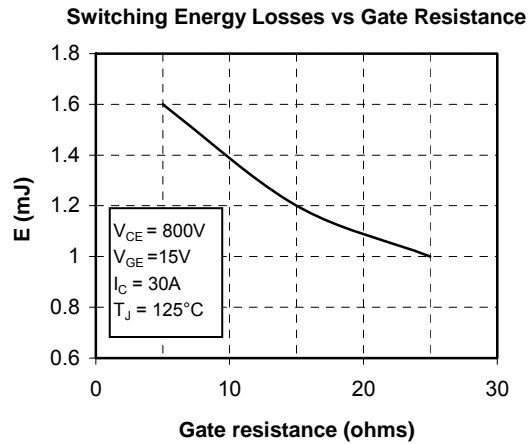
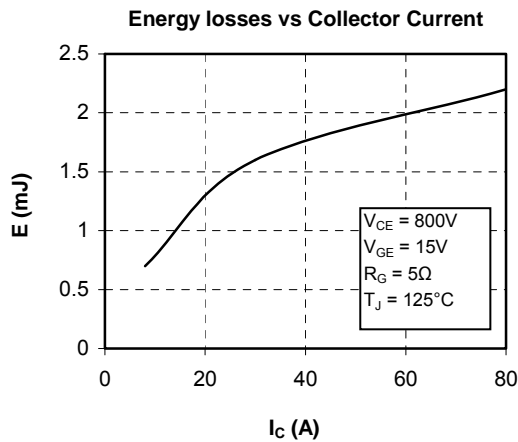
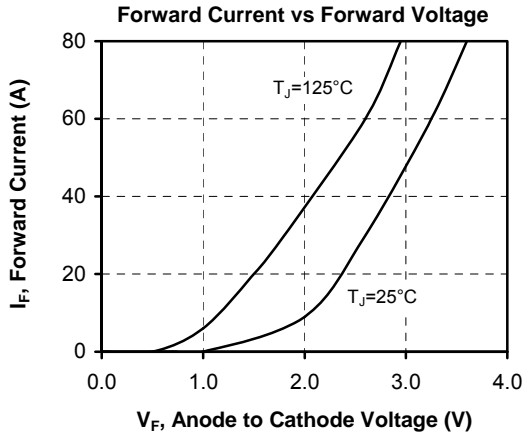
SP3 Package outline (dimensions in mm)


See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com

Q1 to Q4 Typical performance curve




CR1 to CR6 Typical performance curve



Microsemi reserves the right to change, without notice, the specifications and information contained herein

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